

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

Driver Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MMBTA55 MMBTA56, SMMBTA56	V_{CEO}	-60 -80	Vdc
Collector-Base Voltage MMBTA55 MMBTA56, SMMBTA56	V_{CBO}	-60 -80	Vdc
Emitter-Base Voltage	V_{EBO}	-4.0	Vdc
Collector Current - Continuous	I_C	-500	mA _{dc}

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

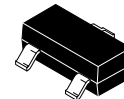
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

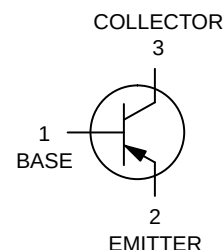


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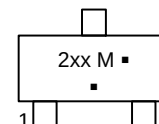
www.onsemi.com



SOT-23
CASE 318
STYLE 6



MARKING DIAGRAM



2xx = Device Code
x = H for MMBTA55LT1G
xx = GM for MMBTA56LT1G,
SMMBTA56LT1G

M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

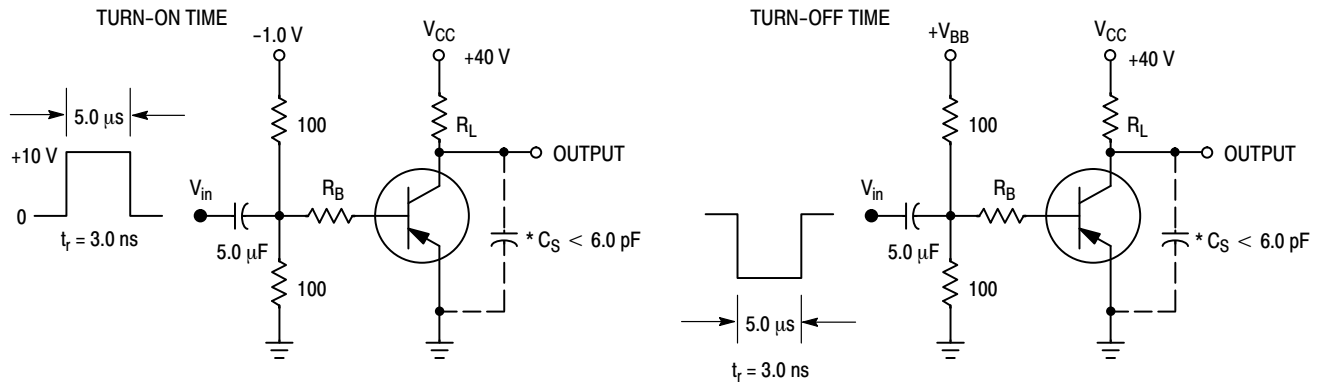
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) ($I_C = -1.0\text{ mA}$, $I_B = 0$) MMBTA55 MMBTA56, SMMBTA56	$V_{(BR)CEO}$	-60 -80	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -100\text{ }\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	-4.0	-	Vdc
Collector Cutoff Current ($V_{CE} = -60\text{ Vdc}$, $I_B = 0$)	I_{CES}	-	-0.1	μAdc
Collector Cutoff Current ($V_{CB} = -60\text{ Vdc}$, $I_E = 0$) MMBTA55 ($V_{CB} = -80\text{ Vdc}$, $I_E = 0$) MMBTA56, SMMBTA56	I_{CBO}	- -	-0.1 -0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = -10\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -100\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	h_{FE}	100 100	- -	-
Collector – Emitter Saturation Voltage ($I_C = -100\text{ mA}$, $I_B = -10\text{ mA}$)	$V_{CE(sat)}$	-	-0.25	Vdc
Base – Emitter On Voltage ($I_C = -100\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	$V_{BE(on)}$	-	-1.2	Vdc
SMALL – SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (Note 4) ($I_C = -100\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	50	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

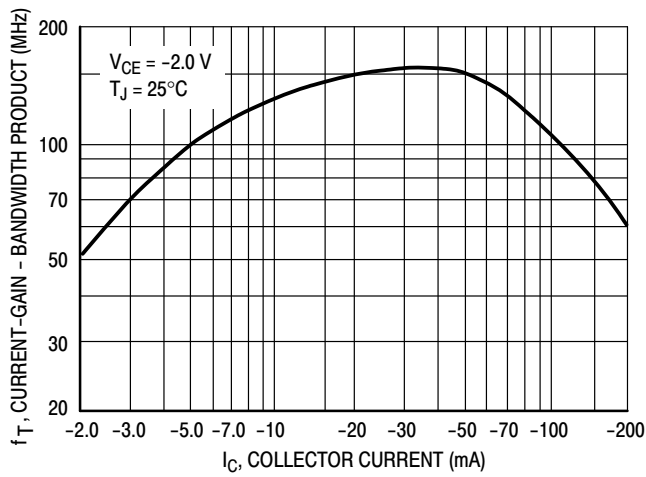


Figure 2. Current-Gain — Bandwidth Product

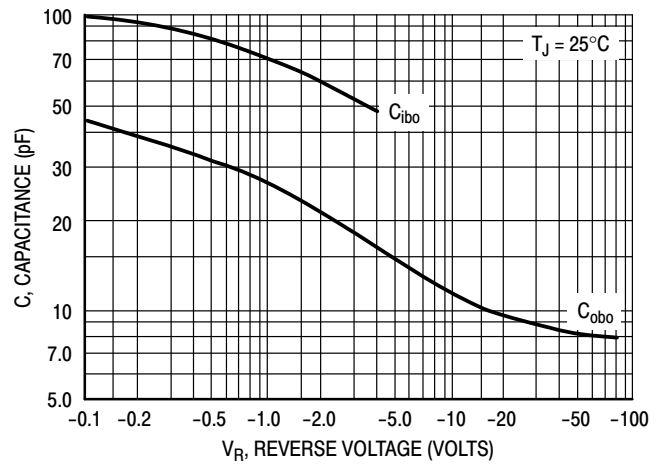


Figure 3. Capacitance

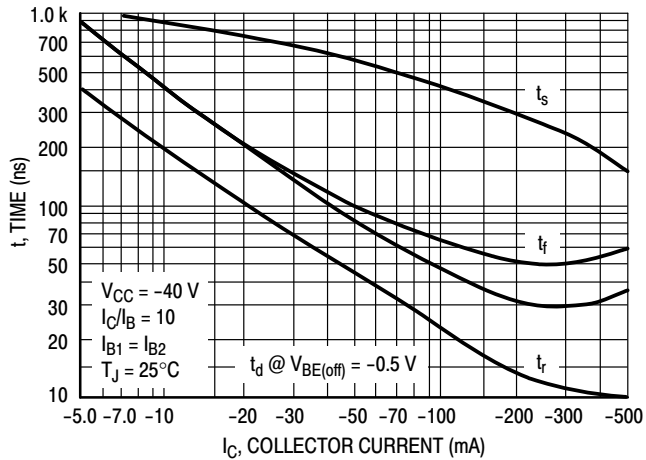


Figure 4. Switching Time

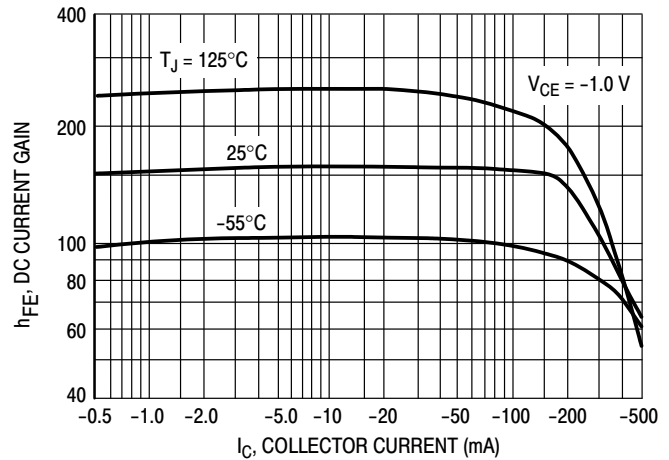


Figure 5. DC Current Gain

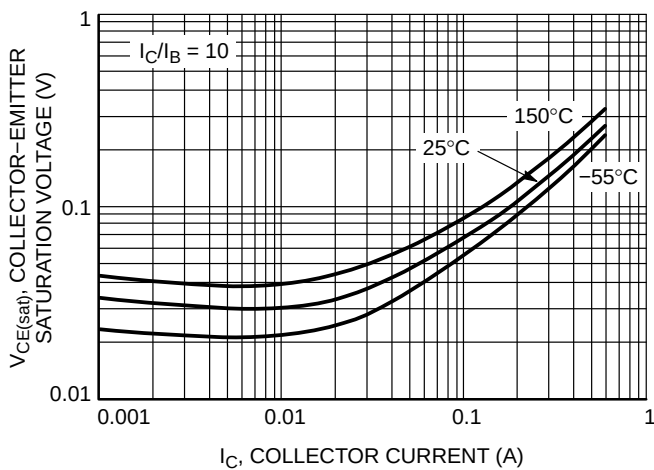


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

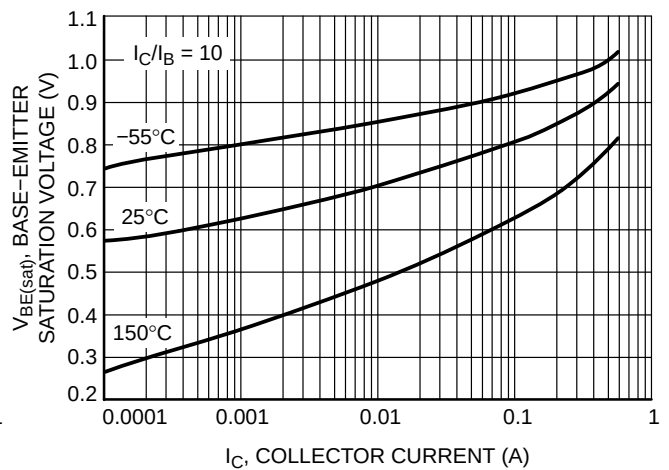


Figure 7. Base Emitter Saturation Voltage vs. Collector Current

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

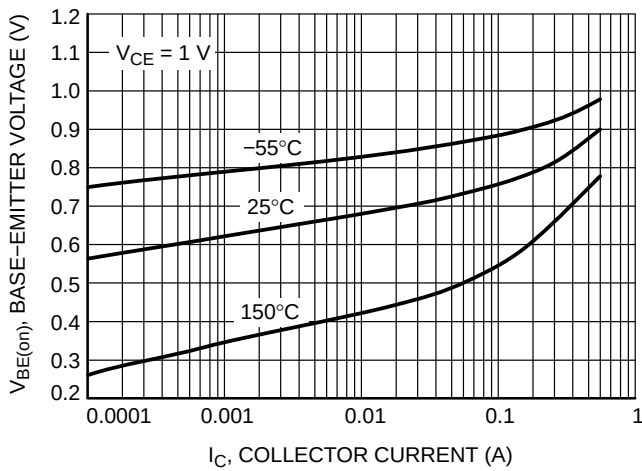


Figure 8. Base-Emitter Voltage vs. Collector Current

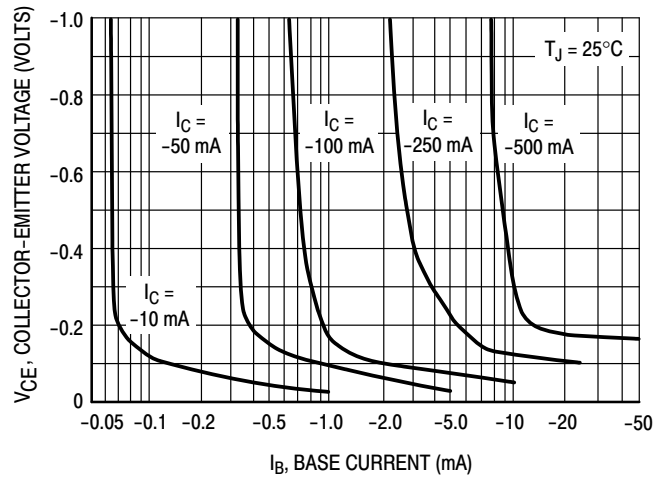


Figure 9. Collector Saturation Region

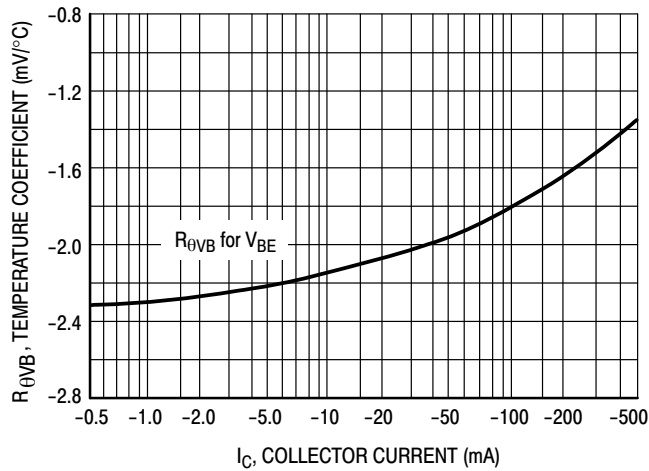


Figure 10. Base-Emitter Temperature Coefficient

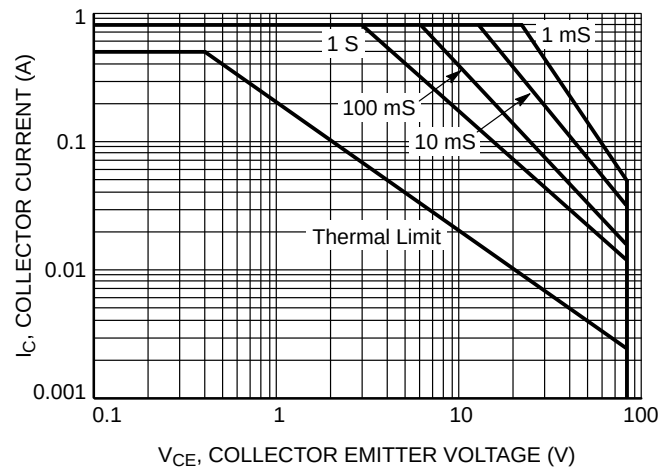


Figure 11. Safe Operating Area

ORDERING INFORMATION

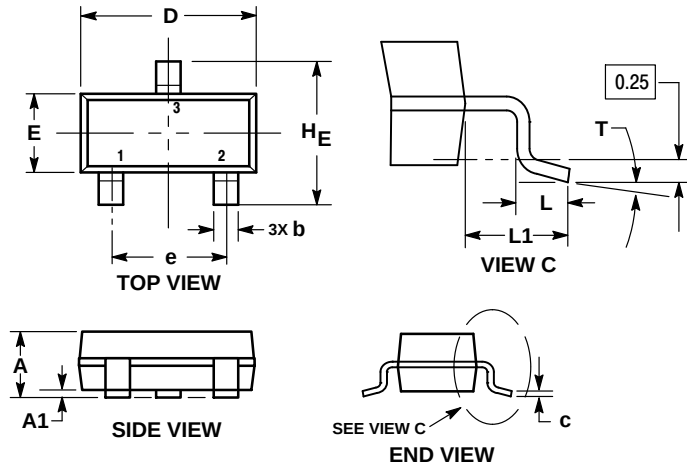
Device Order Number	Package Type	Shipping [†]
MMBTA55LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA55LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA55L Series, MMBTA56L Series, SMMBTA56L Series

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AS



NOTES:

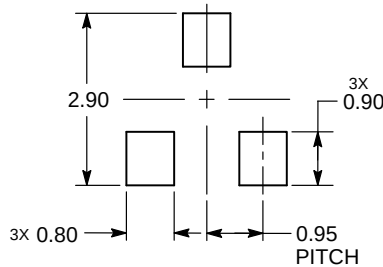
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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